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(54) Title: A PROGRESSIVE TRIMMING METHOD

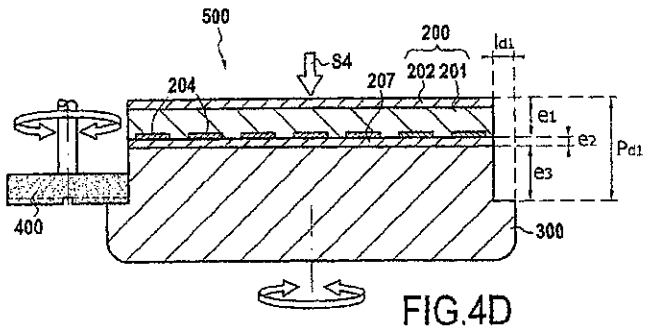


FIG.4D

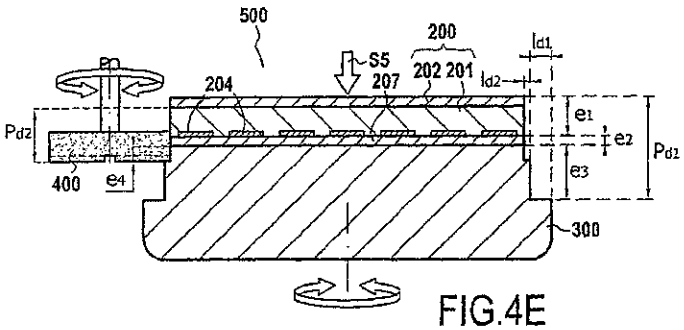


FIG.4E

(57) Abstract: The invention provides a method of trimming a structure (500) comprising a first wafer (200) bonded to a second wafer (300), the first wafer having a chamfered edge. The method comprises a first trimming step (S4) carried out over a first depth (Pd_1) comprising the thickness (e_1) of the first wafer (101) and over a first width ($1d_1$) determined from the edge of the first wafer (101). A second trimming step (S5) is also carried out over a second depth (Pd_2) comprising at least the thickness (e_1) of the first wafer (101) and over a second width ($1d_2$) that is less than the first width ($1d_1$).

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